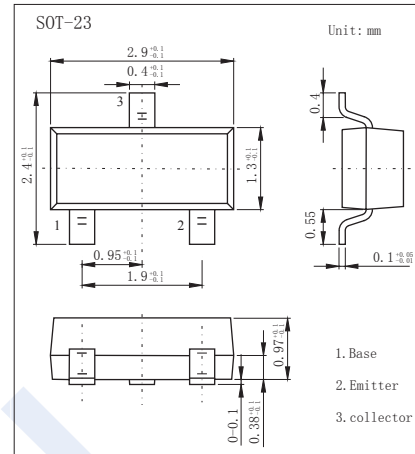


PNP Transistors

2SB1295

■ Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Complimentary to 2SD1935.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-15	V
Collector - Emitter Voltage	V _{CEO}	-15	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-0.8	A
Collector Current - Pulse	I _{CP}	-3	A
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E = 0	-15			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} = ∞	-15			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -12V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -5 mA, I _B = -0.5mA		-10	-25	mV
		I _C = -400 mA, I _B = -20mA		-100	-200	
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -400 mA, I _B = -20mA		-0.9	-1.2	V
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -50mA	135		600	
		V _{CE} = -2V, I _C = -800mA	80			
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		15		pF
Transition frequency	f _T	V _{CE} = -2V, I _E = 50mA		300		MHz

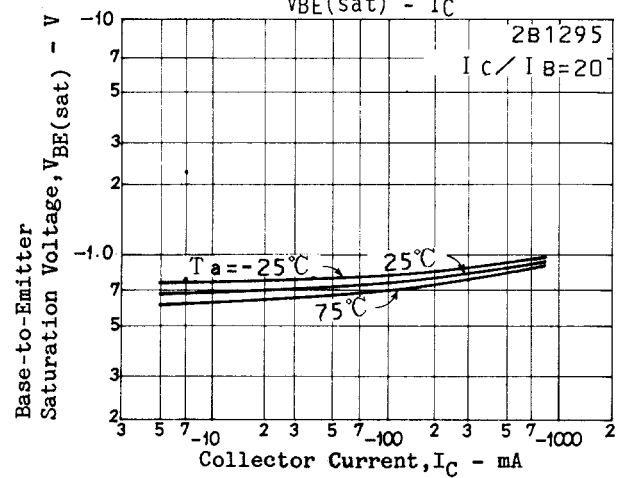
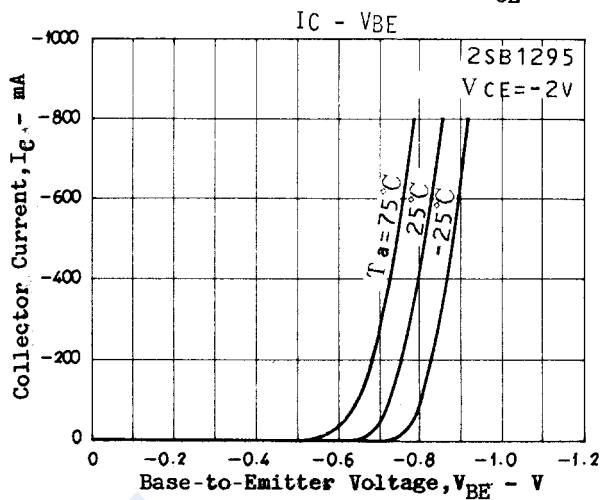
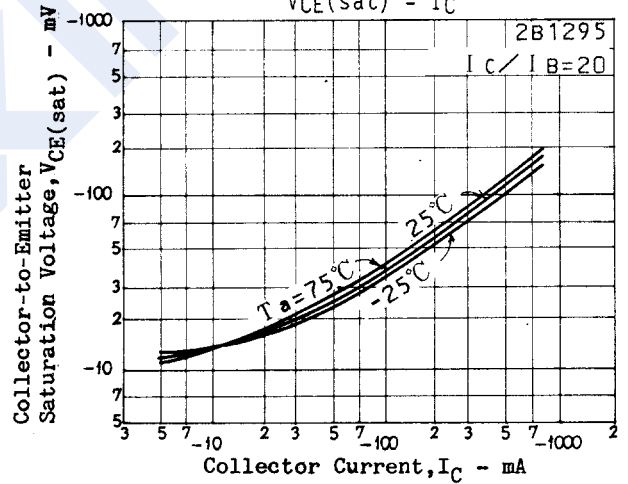
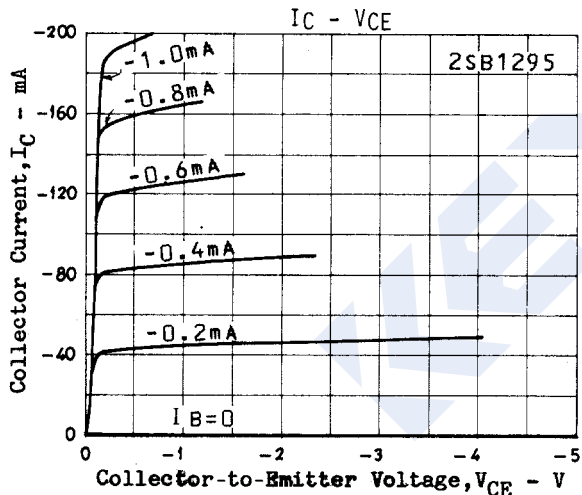
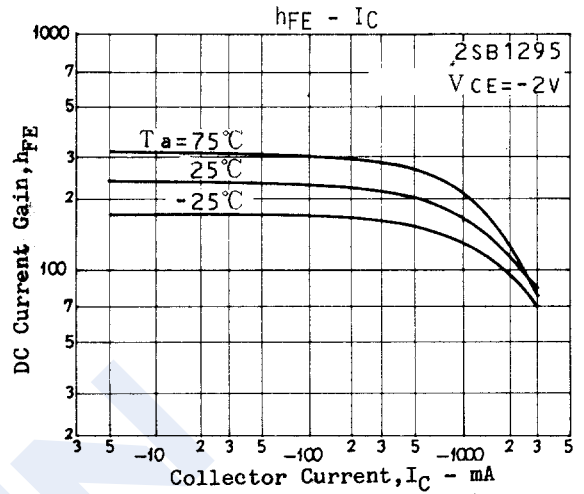
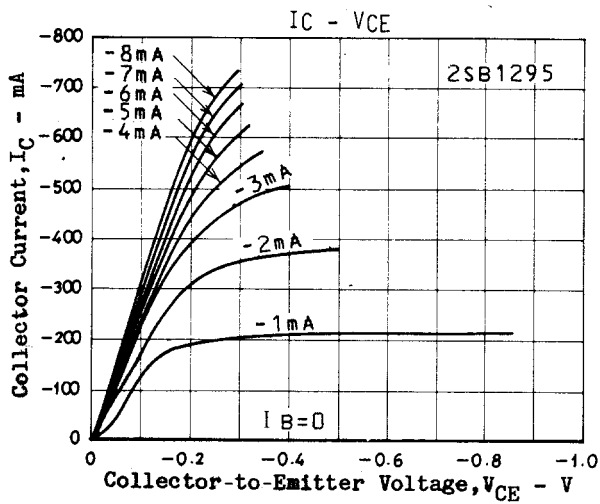
■ Classification of h_{FE}(1)

Type	2SB1295-UL5	2SB1295-UL6	2SB1295-UL7
Range	135-270	200-400	300-600
Marking	UL5	UL6	UL7

PNP Transistors

2SB1295

■ Typical Characteristics



PNP Transistors

2SB1295

■ Typical Characteristics

